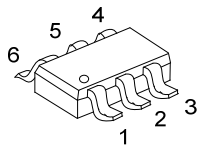
COMPOSITE TRANSISTORS
UT3PP



SOT-363

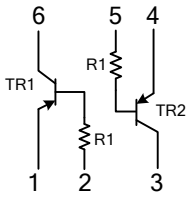
■ DESCRIPTION

As a composite transistor with resistor, the UTC **UT3PP** is for switching application.

■ FEATURES

* Silicon Epitaxial Type
* The Internal Tow Transistor Elements are Independent.

■ SYMBOL

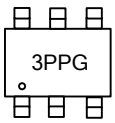


■ ORDERING INFORMATION

Ordering Number	Package	Pin Assignment						Packing
		1	2	3	4	5	6	
UT3PPG-AL6-R	SOT-363	E1	B1	C2	E2	B2	C1	Tape Reel

UT3PPG-AL6-R (1)Packing Type (2)Package Type (3)Halogen Free	(1) R: Tape Reel (2) AL6: SOT-363 (3) G: Halogen Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-100	mA
Peak Collector Current	I_{CM}	-200	mA
Collector Power dissipation	P_C	125	mW
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	−55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_a=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=-100μA	-50			V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C =-10mA ,I_B =-0.5mA			-0.3	V
Collector Cutoff Current	I_{CBO}	V_{CB}=-50V			-0.1	μA
DC Current Transfer Ratio	h_{FE}	V_{CE}=-5V, I_C=-1mA	100			
Transition Frequency	f_T	V_{CE}=-6V, I_E=10mA		150		MHz
Input Resistance	R_1		0.7	1.0	1.3	kΩ